IN THE CLAIMS

Please amend the claims as follows:

1. - 14. (Cancelled)

15. (Original) A method for forming an electrical device comprising:

forming via between a first layer of conductive material and a second layer of conductive material;

lining the via with a conductive material;

connecting the lining to a first conductive layer;

forming a conductor through the via;

connecting the conductor to the first conductive layer;

connecting the lining to the second conductive layer; and

insulating the lining in the via from the conductor in the via.

16. (Original) The method of claim 15 wherein lining the opening with material includes etching the bottom of the opening.

17. (Original) The method of claim15 wherein lining the opening with a material includes lining the opening with a magnetizable material.

18. (Original) The method of claim 15 wherein lining the opening includes lining the opening with conductive material.

19. (Original) A method for forming a device within a via comprising:

forming a via;

depositing a first layer of conductive material on inside surface of the via;

removing a portion of the deposited first layer of conductive material;

depositing a dielectric material onto the remaining portion of the conductive material and onto the inner surface of the via;

removing a second portion of the dielectric material; and

depositing a second layer of conductive material.

20. (Original) The method of claim 19 wherein removing a portion of the deposited first layer includes etching.

21. (Original) The method of claim 19 wherein removing a portion of the deposited insulative material includes etching.

22. (Original) The method of claim 19 wherein the amount of dielectric material provides an insulator between the first conductive layer and the second conductive layer.

23. (Original) A method of forming a device in a via of a substrate comprising:
forming a via;

depositing a first pad having a portion associated with the via;

depositing a second pad having a portion associated with the via, the first pad electrically isolated from the second pad;

filling the via with a resistive material.

24. (Original) The method of claim 23 wherein depositing the first pad and depositing the second includes placement proximate a single surface of the substrate.

25. (Original) The method of claim 23 wherein depositing the first pad includes placement proximate a first surface of the substrate and depositing the second includes placement proximate a second surface of the substrate.

26. (Original) The method of claim 23 wherein the filling the via with a resistive material includes selecting the resistivity of the material to select the resistance across the via.

27. (Original) A method comprising:

forming a via in a substrate; and

forming at least a portion of an electrical component in the via in the substrate.

28. (Original) The method of claim 27 wherein forming at least a portion of an electrical component in the via includes forming a resistor.

29. (Original) The method of claim 27 wherein forming at least a portion of an electrical component in the via includes forming a capacitor.

30. (Original) The method of claim 27 wherein forming at least a portion of an electrical component in the via includes forming a core.

31. (Original) The method of claim 27 wherein forming at least a portion of an electrical component in the via includes forming at least a portion of a transformer.

32. (New) A method comprising:

forming a via in a substrate; and

forming an electrical component in the via in the substrate.

33. (New) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a resistor.

34. (New) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a capacitor.

35. (New) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a core.

36. (New) The method of claim 32 wherein forming an electrical component in the via includes forming a resistor.

37. (New) The method of claim 32 wherein forming an electrical component in the via includes forming a core.

38. (New) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a memory device.

39. (New) The method of claim 32 wherein forming an electrical component in the via includes forming a memory device.

40. (New) The method of claim 32 wherein the electrical component in the via includes a passive electrical component.

41. (New) The method of claim 32 wherein the electrical component in the via is a passive electrical component.

42. (New) The method of claim 32 wherein the electrical component is a capacitor further comprising:

an inner cylindrical portion; and

an outer via portion substantially surrounding the inner cylindrical portion.

43. (New) The method of claim 32 wherein the electrical component is a capacitor further comprising:

a first curved portion; and

a second curved portion spaced from the first curved portion, wherein the distance between the first curved portion and the second curved portion vary.

44. (New) The method of claim 32 wherein the electrical component is a capacitor further comprising:

a first curved portion; and

a second curved portion spaced from the first curved portion, wherein the first curved portion and the second curved portion are portions of a via formed by insulating a first portion of a via from a second portion of a via..

45. (New) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a transformer.